

TOSHIBA Infrared LED GaAs Infrared Emitter

TLN226(F)

Lead(Pb)-Free

For Space-optical-transmission

- High radiant power: $P_o = 18\text{mW}(\text{typ.})$ at $I_f = 50\text{mA}$
- Wide half-angle value: $\theta_{1/2} = \pm 13^\circ(\text{typ.})$
- high-speed response: $t_r, t_f = 30\text{ns}(\text{typ.})$
- Light source for remote control
- Designed for transmission of wireless AV signals purpose.
- Designed for high-speed data transmission

Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Forward current	I_F	100	mA
Pulse forward current	I_{FP}	1000(Note1)	mA
Power dissipation	P_D	220	mW
Reverse voltage	V_R	4	V
Operating temperature	T_{opr}	-25~85	°C
Storage temperature	T_{stg}	-30~100	°C
Soldering temperature (5s)	T_{sol}	260	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

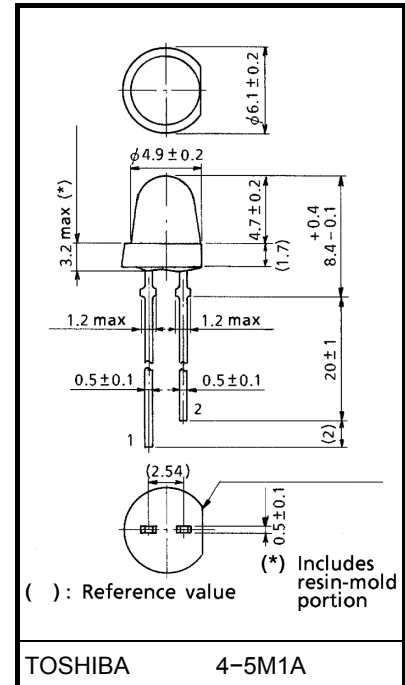
Note 1: Frequency = 100kHz, duty = 1%

Optical And Electrical Characteristics (Ta = 25°C)

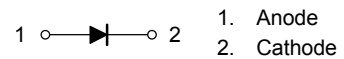
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Forward voltage	V_F	$I_F = 100\text{mA}$	—	1.8	2.2	V
Reverse current	I_R	$V_R = 4\text{V}$	—	—	60	μA
Radiant power	P_O	$I_F = 50\text{mA}$	14	18	—	mW
Radiant intensity	I_E	$I_F = 50\text{mA}$	—	60	—	mW / sr
Rise time, fall time	t_r, t_f	$I_{FP} = 100\text{mA}, P_W = 100\text{ns}$	—	30	—	ns
Cut-off frequency (Note 2)	f_c	$I_F = 50\text{mA}_{DC} + 5\text{mA}_{p-p}$	10	15	—	MHz
Capacitance	C_T	$V_R = 0, f = 1\text{MHz}$	—	110	—	pF
Peak emission wavelength	λ_P	$I_F = 50\text{mA}$	830	870	900	nm
Spectral line half width	$\Delta\lambda$	$I_F = 50\text{mA}$	—	50	—	nm
Half value angle	$\theta_{\frac{1}{2}}$	$I_F = 50\text{mA}$	—	± 13	—	°

Note 2: Frequency when modulation light power decreases by 3dB from 1 MHz.

Unit: mm



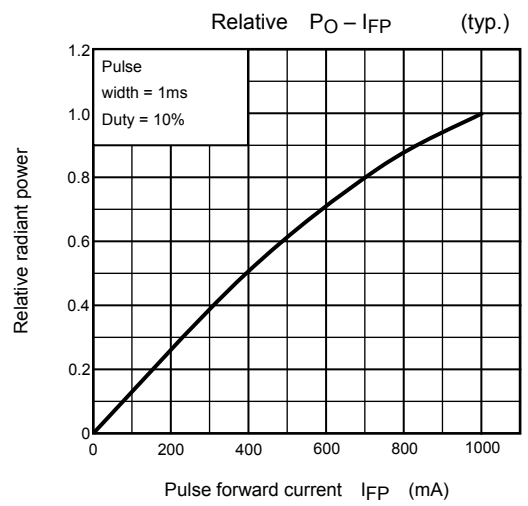
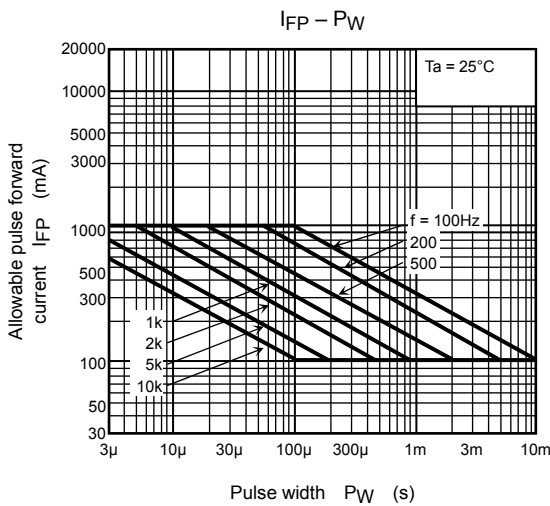
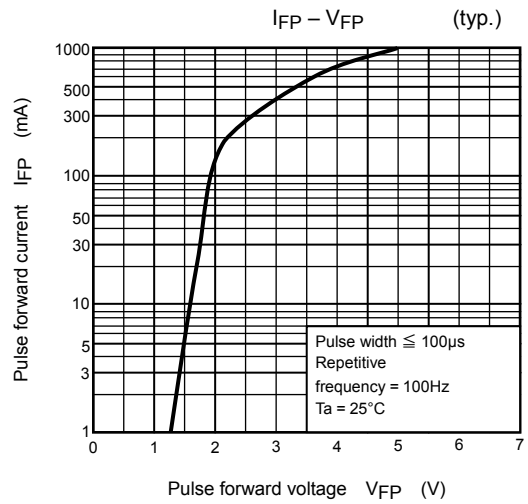
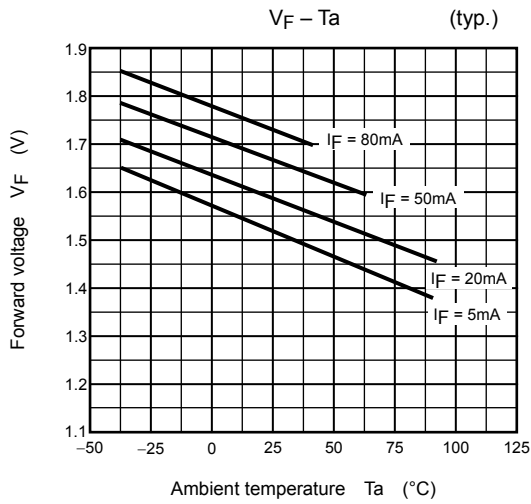
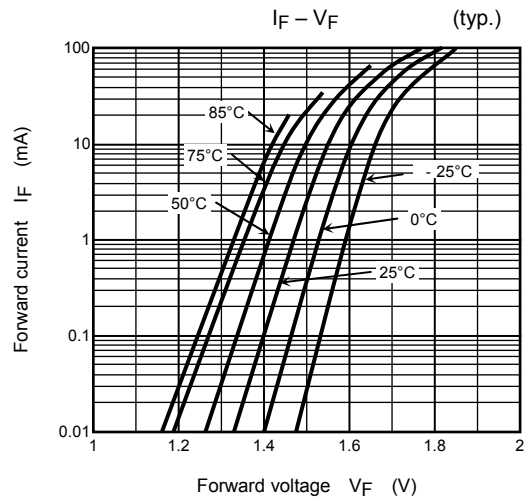
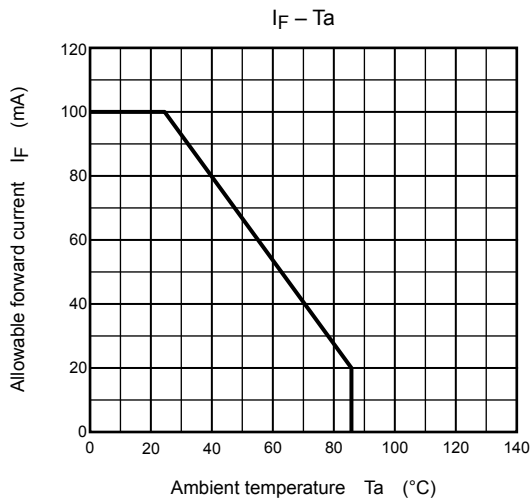
Pin Connection

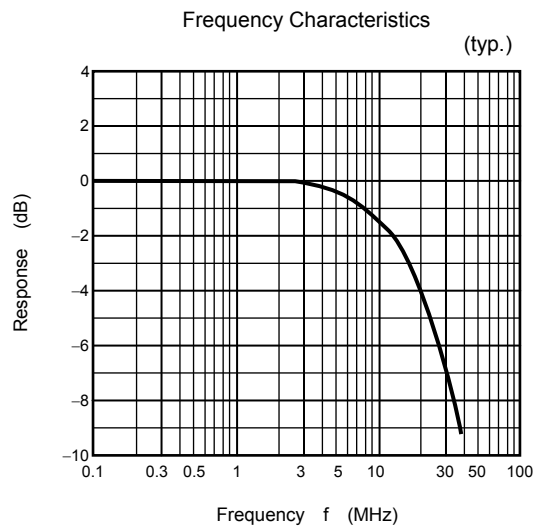
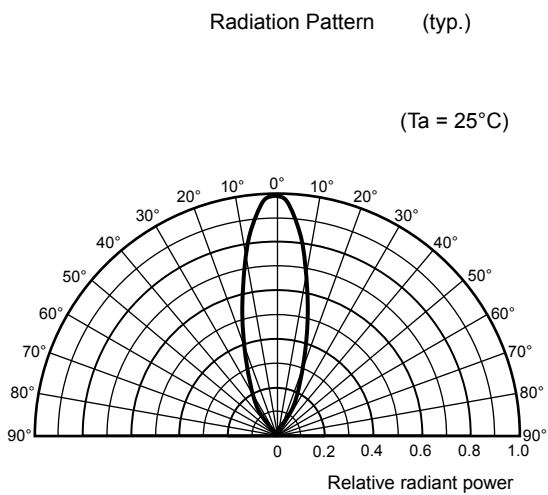
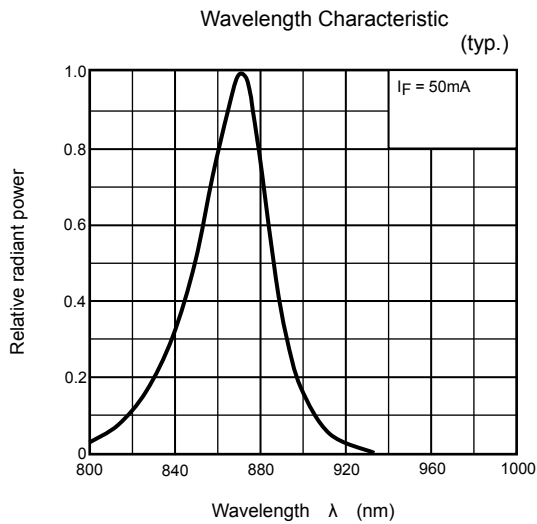
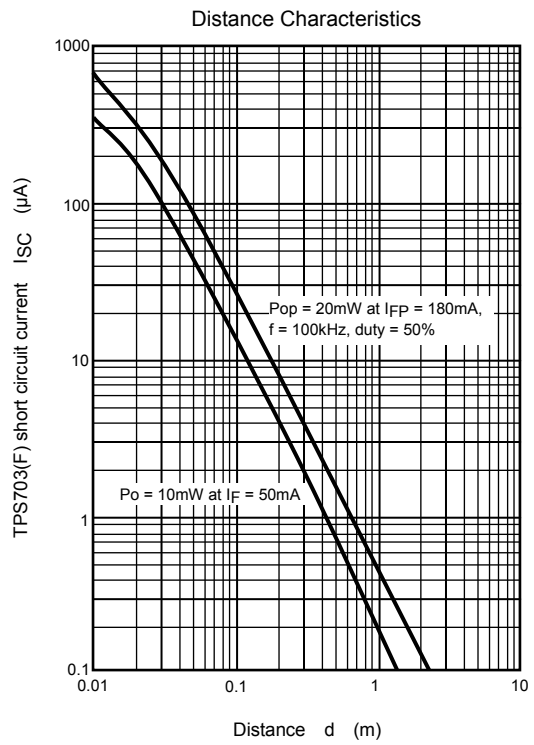
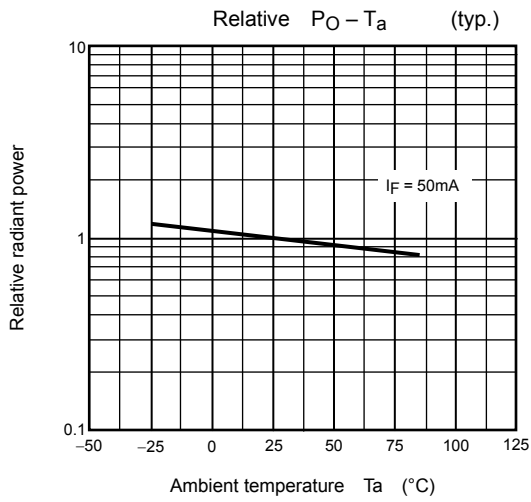


Precautions

Please be careful of the followings

1. Soldering must be performed under the lead stopper.
2. When forming the leads, bend each lead under the stopper without leaving forming stress to the body of the device. Soldering must be performed after the leads have been formed.
3. Radiant power falls over time due to the current which flows in the infrared LED.
When designing a circuit, take into account this change in radiant power over time.





RESTRICTIONS ON PRODUCT USE

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patents or other rights of TOSHIBA or the third parties.
- GaAs(Gallium Arsenide) is used in this product. The dust or vapor is harmful to the human body. Do not break, cut, crush or dissolve chemically.
- Please contact your sales representative for product-by-product details in this document regarding RoHS compatibility. Please use these products in this document in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses occurring as a result of noncompliance with applicable laws and regulations.